**HMC462**

**GaAs pHEMT MMIC LOW NOISE AMPLIFIER, 2 - 20 GHz**

**Typical Applications**
The HMC462 is ideal for:
- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

**Features**
- Noise Figure: 2 dB
- Gain: 15 dB
- P1dB +15.5 dBm
- Self-Biased: +5V @ 63 mA
- 50 Ohm Matched Input/Output
- Die Size: 3.0 x 1.3 x 0.1 mm

**General Description**
The HMC462 is a GaAs MMIC pHEMT Low Noise Distributed Amplifier which operates between 2 and 20 GHz. The amplifier provides 15 dB of small signal gain, 2.5 dB noise figure, and up to +15.5 dBm of output power at 1dB compression. Gain flatness is excellent at ±0.3 dB from 8 - 14 GHz making the HMC462 ideal for EW, ECM, and Radar applications. The HMC462 requires a single supply of +5V @ 63 mA and is the self biased version of the HMC463. The wideband amplifier I/Os are internally matched to 50 Ohms facilitating integration into Multi-Chip-Modules (MCMs). All data is measured with the chip in a 50 Ohm test fixture connected via 0.025 mm (1 mil) diameter wire bonds of 0.31 mm (12 mils) length.

**Functional Diagram**

```
+------------------+
|                  |
|      Vdd        |
|                  |
|      IREF       |
|                  |
|      RFIN       |
|                  |
|      G     +     |
|                  |
|      RFOUT      |
|                  |
|      0          |
```

**Electrical Specifications, T_A = +25° C, Vdd = +5V, Idd = 63 mA**

<table>
<thead>
<tr>
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<tbody>
<tr>
<td>Frequency Range</td>
<td>2 - 8</td>
<td>8 - 16</td>
<td>16 - 20</td>
<td>GHz</td>
<td></td>
<td></td>
<td></td>
<td></td>
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<td></td>
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<tr>
<td>Gain</td>
<td>13.5</td>
<td>15.5</td>
<td>13</td>
<td>15</td>
<td>12.5</td>
<td>14.5</td>
<td>dB</td>
<td></td>
<td></td>
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<tr>
<td>Gain Flatness</td>
<td>±0.2</td>
<td>±0.3</td>
<td>±0.2</td>
<td>dB</td>
<td></td>
<td></td>
<td></td>
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</tr>
<tr>
<td>Gain Variation Over Temperature</td>
<td>0.005</td>
<td>0.011</td>
<td>0.019</td>
<td>dB/°C</td>
<td></td>
<td></td>
<td></td>
<td></td>
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<td></td>
</tr>
<tr>
<td>Input Return Loss</td>
<td>16</td>
<td>19</td>
<td>16</td>
<td>dB</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Output Return Loss</td>
<td>18</td>
<td>19</td>
<td>18</td>
<td>dB</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Output Power for 1 dB Compression</td>
<td>12.5</td>
<td>15.5</td>
<td>11.5</td>
<td>dBm</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Saturated Output Power (Psat)</td>
<td>18</td>
<td>17</td>
<td>15.5</td>
<td>dBm</td>
<td></td>
<td></td>
<td></td>
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<td></td>
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</tr>
<tr>
<td>Output Third Order Intercept (IP3)</td>
<td>26</td>
<td>25</td>
<td>24</td>
<td>dBm</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Noise Figure</td>
<td>3</td>
<td>2.5</td>
<td>2.5</td>
<td>dB</td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
<td></td>
</tr>
<tr>
<td>Supply Current (Idd)</td>
<td>41</td>
<td>63</td>
<td>84</td>
<td>mA</td>
<td></td>
<td></td>
<td></td>
<td></td>
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GaAs pHEMT MMIC
LOW NOISE AMPLIFIER, 2 - 20 GHz

Gain & Return Loss

Gain vs. Temperature

Input Return Loss vs. Temperature

Output Return Loss vs. Temperature

Reverse Isolation vs. Temperature

Noise Figure vs. Temperature

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HMC462

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P1dB vs. Temperature

Psat vs. Temperature

P1dB vs. Vdd

Psat vs. Vdd

Output IP3 vs. Temperature
@ Pout = 4 dBm Tone

Output IP3 vs. Vdd
@ Pout = 4 dBm Tone

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15 18 21 24 27 30
2 4 6 8 10 12 14 16 18 20 22

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Phone: 978-250-3343     Fax: 978-250-3373     Order On-line at www.hittite.com
Application Support: Phone: 978-250-3343  or  apps@hittite.com
GaAs pHEMT MMIC
LOW NOISE AMPLIFIER, 2 - 20 GHz

**Power Compression @ 4 GHz**

![Power Compression @ 4 GHz graph]

**Power Compression @ 12 GHz**

![Power Compression @ 12 GHz graph]

**Power Compression @ 20 GHz**

![Power Compression @ 20 GHz graph]

**Power Dissipation**

![Power Dissipation graph]

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Absolute Maximum Ratings

<table>
<thead>
<tr>
<th>Parameter</th>
<th>Specification</th>
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<tbody>
<tr>
<td>Drain Bias Voltage (Vdd)</td>
<td>+9 Vdc</td>
</tr>
<tr>
<td>RF Input Power (RFIN)</td>
<td>+18 dBm</td>
</tr>
<tr>
<td>Channel Temperature</td>
<td>175 °C</td>
</tr>
<tr>
<td>Continuous Pdiss (T= 85 °C) (derate 24.4 mW/°C above 85 °C)</td>
<td>2.2 W</td>
</tr>
<tr>
<td>Thermal Resistance (channel to die bottom)</td>
<td>41 °C/W</td>
</tr>
<tr>
<td>Storage Temperature</td>
<td>-65 to 150 °C</td>
</tr>
<tr>
<td>Operating Temperature</td>
<td>-55 to 85 °C</td>
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</table>

Typical Supply Current vs. Vdd

<table>
<thead>
<tr>
<th>Vdd (V)</th>
<th>Idd (mA)</th>
</tr>
</thead>
<tbody>
<tr>
<td>4</td>
<td>64</td>
</tr>
<tr>
<td>5</td>
<td>66</td>
</tr>
<tr>
<td>6</td>
<td>68</td>
</tr>
<tr>
<td>7</td>
<td>70</td>
</tr>
<tr>
<td>8</td>
<td>72</td>
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</tbody>
</table>

ELECTROSTATIC SENSITIVE DEVICE
OBSERVE HANDLING PRECAUTIONS

Outline Drawing

Die Packaging Information

<table>
<thead>
<tr>
<th>Standard</th>
<th>Alternate</th>
</tr>
</thead>
<tbody>
<tr>
<td>GP-1 (Gel Pack)</td>
<td>[1]</td>
</tr>
</tbody>
</table>

[1] For more information refer to the “Packaging Information” Document in the Product Support Section of our website.

NOTES:
1. ALL DIMENSIONS ARE IN INCHES [MM]
2. DIE THICKNESS IS 0.004"
3. TYPICAL BOND PAD IS 0.004" SQUARE
4. BOND PAD METALIZATION: GOLD
5. BACKSIDE METALIZATION: GOLD
6. BACKSIDE METAL IS GROUND
7. NO CONNECTION REQUIRED FOR UNLABELED BOND PADS
8. OVERALL DIE SIZE ±0.002"

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**Pad Descriptions**

<table>
<thead>
<tr>
<th>Pad Number</th>
<th>Function</th>
<th>Description</th>
<th>Interface Schematic</th>
</tr>
</thead>
<tbody>
<tr>
<td>1</td>
<td>RFIN</td>
<td>This pad is AC coupled and matched to 50 Ohms</td>
<td><img src="image1" alt="Interface Schematic" /></td>
</tr>
<tr>
<td>2</td>
<td>Vdd</td>
<td>Power supply voltage for the amplifier. External bypass capacitors are required</td>
<td><img src="image2" alt="Interface Schematic" /></td>
</tr>
<tr>
<td>3</td>
<td>RFOUT</td>
<td>This pad is AC coupled and matched to 50 Ohms</td>
<td><img src="image3" alt="Interface Schematic" /></td>
</tr>
<tr>
<td>Die Bottom</td>
<td>GND</td>
<td>Die bottom must be connected to RF/DC ground.</td>
<td><img src="image4" alt="Interface Schematic" /></td>
</tr>
</tbody>
</table>

**Assembly Diagram**

![Assembly Diagram](image5)

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Mounting & Bonding Techniques for Millimeterwave GaAs MMICs

The die should be attached directly to the ground plane eutectically or with conductive epoxy (see HMC general Handling, Mounting, Bonding Note).

50 Ohm Microstrip transmission lines on 0.127mm (5 mil) thick alumina thin film substrates are recommended for bringing RF to and from the chip (Figure 1). If 0.254mm (10 mil) thick alumina thin film substrates must be used, the die should be raised 0.150mm (6 mils) so that the surface of the die is coplanar with the surface of the substrate. One way to accomplish this is to attach the 0.102mm (4 mil) thick die to a 0.150mm (6 mil) thick molybdenum heat spreader (moly-tab) which is then attached to the ground plane (Figure 2).

Microstrip substrates should be located as close to the die as possible in order to minimize bond wire length. Typical die-to-substrate spacing is 0.076mm to 0.152 mm (3 to 6 mils).

Handling Precautions

Follow these precautions to avoid permanent damage.

Storage: All bare die are placed in either Waffle or Gel based ESD protective containers, and then sealed in an ESD protective bag for shipment. Once the sealed ESD protective bag has been opened, all die should be stored in a dry nitrogen environment.

Cleanliness: Handle the chips in a clean environment. DO NOT attempt to clean the chip using liquid cleaning systems.

Static Sensitivity: Follow ESD precautions to protect against $\pm 250$V ESD strikes.

Transients: Suppress instrument and bias supply transients while bias is applied. Use shielded signal and bias cables to minimize inductive pick-up.

General Handling: Handle the chip along the edges with a vacuum collet or with a sharp pair of bent tweezers. The surface of the chip may have fragile air bridges and should not be touched with vacuum collet, tweezers, or fingers.

Mounting

The chip is back-metallized and can be die mounted with AuSn eutectic preforms or with electrically conductive epoxy. The mounting surface should be clean and flat.

Eutectic Die Attach: A 80/20 gold tin preform is recommended with a work surface temperature of 255 °C and a tool temperature of 265 °C. When hot 90/10 nitrogen/hydrogen gas is applied, tool tip temperature should be 290 °C. DO NOT expose the chip to a temperature greater than 320 °C for more than 20 seconds. No more than 3 seconds of scrubbing should be required for attachment.

Epoxy Die Attach: Apply a minimum amount of epoxy to the mounting surface so that a thin epoxy fillet is observed around the perimeter of the chip once it is placed into position. Cure epoxy per the manufacturer’s schedule.

Wire Bonding

Ball or wedge bond with 0.025mm (1 mil) diameter pure gold wire. Thermosonic wirebonding with a nominal stage temperature of 150 °C and a ball bonding force of 40 to 50 grams or wedge bonding force of 18 to 22 grams is recommended. Use the minimum level of ultrasonic energy to achieve reliable wirebonds. Wirebonds should be started on the chip and terminated on the package or substrate. All bonds should be as short as possible <0.31mm (12 mils).
Notes: